$$R_H = \frac{6}{t_0}$$
,  $\epsilon = -\frac{\lambda_N}{2t_0}$ .

 $t_0$  and  $\lambda_N$  are free parameters. The figure shows plots of the function (1 - F)q<sup>2</sup>, constructed with the aid of (10) and (11) for certain values of the parameters  $\lambda_N$  and  $t_0$ . For comparison, the same figure shows the experimental data obtained from e-p scattering for the quantity (1 - F)q2 and the curves (dashed) with the aid of which these data were approximated in [1].

Thus, the existence of the virtual level in the p-wave of a two-pion system can lead to the occurrence of a proton halo (and just as well to a pion halo). We note that this level, if it does exist, should become manifest also in the processes  $\pi\pi \to \pi\pi$ ,  $\gamma\pi \to \pi\pi$ ,  $\pi N \rightarrow \pi N$ ,  $\gamma N \rightarrow \pi N$ , etc., a study of which, in principle, could yield information concerning this level in addition to data on e-p scattering.

In conclusion we note that virtual levels can exist in principle in a three-pion system, leading to the existence of a halo of the isoscalar part of the nucleon.

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## PHOTOCURRENT IN A SEMICONDUCTOR WITHOUT A SYMMETRY CENTER

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We report in this note that, unlike usual photoconductivity, a photocurrent is produced in a semiconductor without a symmetry center also in the absence of a constant field. Indeed, in a crystal without a symmetry center, a connection is possible between the current and the electromagnetic field; this connection is quadratic in the field and is described by a crossconductivity tensor  $\sigma_{\alpha\beta}(\omega_1, \omega_2)$ . Then the photocurrent is given by the tensor [1]

$$\sigma_{\mu\alpha} \beta (\omega, -\omega) = \frac{e}{2\hbar} \sum_{nk} f_n(k) \nabla_k^{\mu} \chi_{\beta\alpha}^{nk}(\omega). \tag{1}$$

Here  $\mu$ ,  $\alpha$ , and  $\beta$  - projections on the x, y, and z axes, e and h - electron charge and Planck's constant,  $f_n(\vec{k})$  - the Fermi function normalized to the total number of electrons, n and  $\hbar k$  number of the band and the quasimomentum,  $\chi^{nk}_{\beta\alpha}(\omega)$  - linear susceptibility of the Bloch electron in the state  $|n\vec{k}\rangle = u_{nk} \exp(i\vec{k}r)$  with energy  $\epsilon_n(\vec{k})$ , and  $\omega$  - frequency.

The nonlinear mechanism leading to the aforementioned tensor is the combined motion of the electron, namely the interband-intraband motion [1]. Since  $f_n(\vec{k})$  is even, the tensor (1) vanishes when  $\alpha = \beta$  as  $\vec{k} \rightarrow -\vec{k}$ , regardless of the crystal symmetry type.

We consider further the particular case of a wave propagating along the z axis, with  $E_x = E_0 \cos \omega_t$  and  $E_y = E_0 \cos (\omega t + \phi)$ , where  $E_0$  is the field amplitude and  $\phi$  the phase shift. For concreteness we assume that the semiconductor has one partly-filled conduction band (c-band) and the remaining valence bands are completely filled (v-bands). Then the contribution to the valence bands is additive, and we can confine ourselves to calculation of the maximum contribution, putting  $\omega \sim \omega_g$  and  $\omega \ll \omega_g'$ , where  $\omega_g$  and  $\omega_g'$  are respectively the energy gaps between the c-band and the band under consideration, and between the c-band and the discarded valence bands. Replacing the summation over k by integration with the distribution function for a strongly degenerate semiconductor, we obtain for the photocurrent density

$$i_{\mu} = \frac{ie^{3} n_{0} \sin \phi E_{0}^{2}}{4\hbar^{2}} \left(\frac{\partial M_{xy}}{\partial k_{\mu}}\right) \left[\frac{\omega_{g} - \omega + \Delta(k_{F})}{(\omega_{g} - \omega + \Delta(k_{F}))^{2} + \gamma^{2}} - \frac{\omega_{g} + \omega + \Delta(k_{F})}{(\omega_{g} + \omega + \Delta(k_{F}))^{2} + \gamma^{2}}\right], \tag{2}$$

where  $n_0$  is the electron density,  $\gamma$  is the phenomenologically introduced damping constant,  $k_F$  is the quasimomentum corresponding to the band-filling limit, and the derivative of the quantity

$$M_{xy}(k) = \Omega_{cy}^{x}(k)\Omega_{yc}^{y}(k) - \Omega_{cy}^{y}(k)\Omega_{vc}^{x}(k)$$

is taken at k = 0 and  $\Delta(k_F) = (\hbar/2m_{\rm cv}^*)k_F^2$ . It is seen from (2) that j<sub>\mu</sub> is proportional to  $\sin \varphi$ , i.e., the photocurrent depends strongly on the relative phase shifts between the electric field components. j<sub>\mu</sub> \to 0 when  $\omega < \omega_g$  and j<sub>\mu</sub> increases with increasing  $\omega$  and decreases like  $1/\omega$  when  $\omega > \omega_g$ . The maximum value of j<sub>\mu</sub> is determined also by the quantity  $\Delta(k_F)$ , which is connected with the finite width of the filled section of the c-band. The indicated features of the phenomenon make it possible to observe it experimentally. Let us estimate the effect, using the parameters of GaAs, namely  $\omega$  = 2.1 x  $10^{15}$  rad/sec ( $\hbar\omega$  = 1.37 eV) and  $n_O$  = 5 x  $10^{17}$  cm<sup>-3</sup>. At a frequency  $\omega$  = 1.8 x  $10^{15}$  rad/sec ( $\hbar\omega$  = 1.17 eV, neodymium laser), the shift  $\Delta(k_F)$  and the broadening  $\gamma$  can be neglected even at room temperature, and as a result we have

$$j_z \approx 3 \times 10^6 E_0^2 \text{ g}^{-1/2} - \text{cm}^{1/2}$$
 (3)

In (3),  $E_0$  is a dimensional unit in the cgs esu system. In the practical unit system we get  $j_z \sim 1~\mathrm{A/cm^2}$  at  $E_0 \sim 10^4~\mathrm{V/cm}$ . It is convenient to introduce  $E_z^{\mathrm{eff}} = j_z/\sigma_0$ , where  $\sigma_0$  is the static conductivity. Then the potential difference between the faces of a single crystal of length 1 along the z axis is  $U = E_z^{\mathrm{eff}}$ 1. When 1 = 0.1 cm and  $\sigma_0 \sim 10^2~\mathrm{ohm^{-1}cm^{-1}}$  we get  $U \sim 10^{-3}~\mathrm{V}$ , i.e., a readily observable quantity. For a semiconductor with a narrow forbidden band, such as InSb, a suitable source may be a  $\mathrm{CO}_2$  laser ( $\lambda = 10.6~\mu$ ). Application of a magnetic field  $\dot{H}$  leads to new singularities of the photocurrent. In particular, photocurrent directions  $\mu \neq z$  become possible even for cubic crystals. We note here that for the z-component we have  $j_z' = (j_z/n_0)Z(\zeta)$ , where  $\zeta = \varepsilon_F/\hbar\omega_C$ ,  $\omega_C = \mathrm{eH/mc}$  is the cyclotron frequency, m is the effective mass in the conduction band, and  $\varepsilon_F$  is the Fermi level reckoned from the

bottom of the band.  $Z(\zeta)$  is the number of states per unit volume having an energy lower than  $\epsilon_F$  and, as is well known, oscillates as a function of  $H^{-1}$ . Thus, photocurrent oscillations take place in a magnetic field.

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\* The matrix elements  $\Omega_{cv}(\vec{k})$  are defined, for example, in [1]. We are considering crystals with  $\Omega_{cc}(\vec{k})=0$ .

METHOD FOR DIRECT OBSERVATION OF THE GIANT MAGNETIC FIELDS PRODUCED AT A NUCLEUS BY A HOLE IN THE K SHELL

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The probability that a nucleus will emit a particle or a quantum in a certain direction depends, in the general case, as is well known, on the angle between this direction and the nuclear spin I (I  $\geq$  1). For this reason, in the case of a nuclear decay sequence  $A^a \rightarrow B^b \rightarrow C$  the spins  $I_B$  of the intermediate nuclei B are not isotropically distributed in space relative to the preferred direction of the registration of particle a. The anisotropy of the orientation of the spins  $I_B$  causes in turn the probability W of coincidence of the registration of two particles a and b by two counters  $C_a$  and  $C_b$  to depend on the angle  $\theta_{ab}$  between the emission directions:

$$W(\theta_{ab}) = \sum_{i=0}^{i_{max}} \alpha_i \cos^{2i} \theta_{ab},$$

where  $I_{max}$  is double the value of the smallest of the three quantities  $I_a$ ,  $I_b$  (the angular momenta carried by the particles a and b), and  $I_a$ .

This correlation between the directions of a and b is upset (perturbation of the angular correlations) when a noticeable precession of the magnetic (or quadrupole) moment of the intermediate nucleus B can be produced during its lifetime  $\tau_B$  in the magnetic (or inhomogeneous electric) fields by the molecular or crystalline environment of the nucleus. In the presence of such a precession, the nucleus B will "forget", by the instant of the emission of b, the direction of  $I_B$  at the instant of emission of a and formation of B. The sensitivity of experiments aimed at the observation of the perturbed angular correlations ensures the possibility of investigating on their basis local magnetic  $(H_N)$  and electric  $(q_N)$  fields at the nuclei if  $\omega_B \tau_B \gtrsim 0.01$  ( $\omega_B$  - precession frequency of  $I_B$ ), corresponding to  $\tau_B \gtrsim 10^{-11}$  sec for the customary values  $H_N \approx 10^5$  Oe and  $q_N \approx 10^{18}$  V/cm² (see [1], Part II, Sec. 8).

The cited values of the local magnetic fields at the nuclei are much lower than the maximum possible ones that are realizable in the presence of a hole in the K shell.